

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Application Serial No. .... 10/636,038  
Confirmation No. .... 9972  
Filing Date ..... August 6, 2003  
Inventor..... Gurtej S. Sandhu  
Assignee..... Micron Technology, Inc.  
Group Art Unit..... 1762  
Examiner ..... Chen, Bret P.  
Attorney's Docket No. .... MI22-2194  
Customer No. .... 021567  
Title: Methods of Forming Material on a Substrate, and Method of Forming a  
Field Effect Transistor Gate Oxide on a Substrate

**RESPONSE TO NOVEMBER 28, 2006 FINAL OFFICE ACTION**

To: Mail Stop AF  
Commissioner for Patents  
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**AMENDMENTS**

In response to the Final Office Action of November 28, 2006, applicant amends and remarks as follows.